
2SJ175

Silicon P-Channel MOS FET

HITACHI

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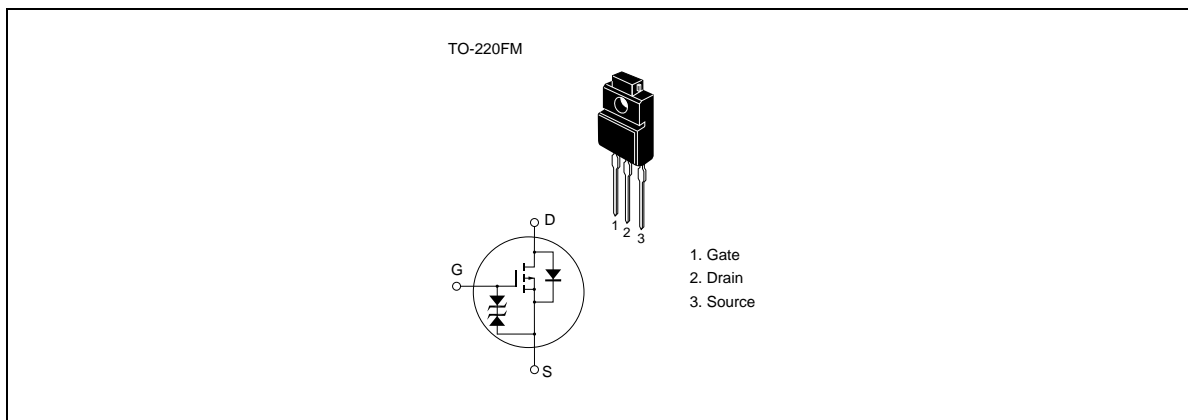
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline



2SJ175

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|---|---------------------|-------------|------|
| Drain to source voltage | V_{DSS} | -60 | V |
| Gate to source voltage | V_{GSS} | ±20 | V |
| Drain current | I_D | -10 | A |
| Drain peak current | $I_{D(pulse)}^{*1}$ | -40 | A |
| Body to drain diode reverse drain current | I_{DR} | -10 | A |
| Channel dissipation | Pch^{*2} | 25 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

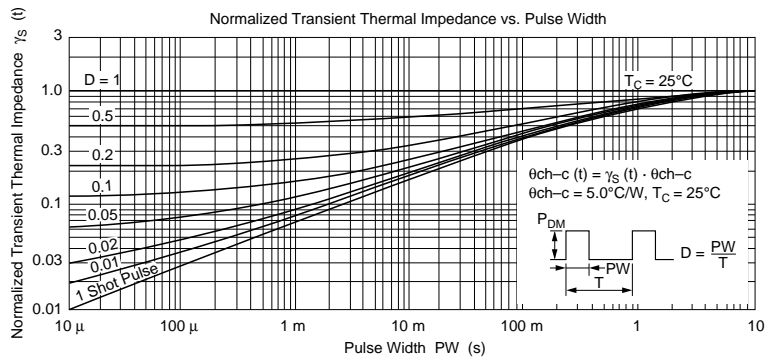
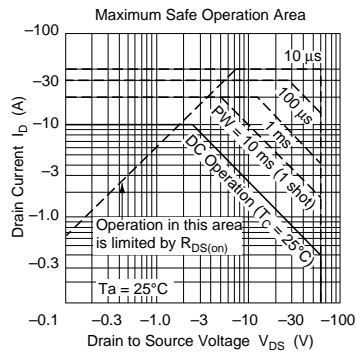
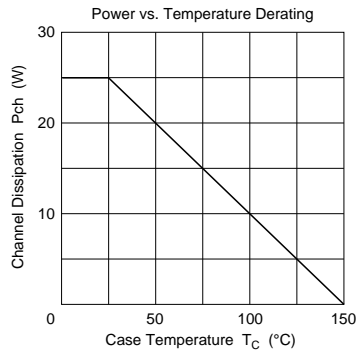
Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|--|---------------|----------|------|----------|---------------|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | -60 | — | — | V | $I_D = -10 \text{ mA}, V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ± 20 | — | — | V | $I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ± 10 | μA | $V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | -250 | μA | $V_{DS} = -50 \text{ V}, V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | -1.0 | — | -2.0 | V | $I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 0.13 | 0.18 | Ω | $I_D = -5 \text{ A}, V_{GS} = -10 \text{ V}^{*1}$ |
| | | — | 0.18 | 0.25 | | $I_D = -5 \text{ A}, V_{GS} = -4 \text{ V}^{*1}$ |
| Forward transfer admittance | $ y_{fs} $ | 4.0 | 6.5 | — | S | $I_D = -5 \text{ A}, V_{DS} = -10 \text{ V}^{*1}$ |
| Input capacitance | C_{iss} | — | 900 | — | pF | $V_{DS} = -10 \text{ V}, V_{GS} = 0,$ $f = 1 \text{ MHz}$ |
| Output capacitance | C_{oss} | — | 460 | — | pF | |
| Reverse transfer capacitance | C_{rss} | — | 130 | — | pF | |
| Turn-on delay time | $t_{d(on)}$ | — | 8 | — | ns | $I_D = -5 \text{ A}, V_{GS} = -10 \text{ V},$ $R_L = 6 \text{ }\Omega$ |
| Rise time | t_r | — | 65 | — | ns | |
| Turn-off delay time | $t_{d(off)}$ | — | 170 | — | ns | |
| Fall time | t_f | — | 105 | — | ns | |
| Body to drain diode forward voltage | V_{DF} | — | -1.1 | — | V | $I_F = -10 \text{ A}, V_{GS} = 0$ |
| Body to drain diode reverse recovery time | t_{rr} | — | 200 | — | ns | $I_F = -10 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$ |

Note 1. Pulse test

See characteristic curves of 2SJ172



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